

# SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

# TIG058E8 — N-Channel IGBT Light-Controlling Flash Applications

#### **Features**

- · Low-saturation voltage
- · Enhansment type
- · Mounting Height 0.9mm, Mounting Area 8.12mm<sup>2</sup>
- · Halogen free compliance

- · Low voltage drive (4V)
- · Built-in Gate-to-Emitter protection diode
- · dv / dt guarantee\*

# **Specifications**

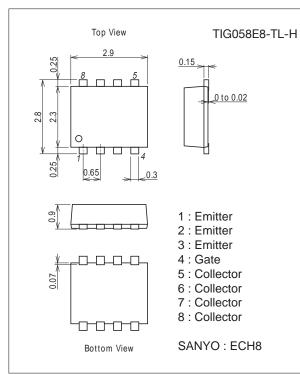
#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Emitter Voltage	VCES		400	V
Gate-to-Emitter Voltage (DC)	VGES		±6	V
Gate-to-Emitter Voltage (Pulse)	VGES	PW≤1ms	±8	V
Collector Current (Pulse)	ICP	C <sub>M</sub> =150μF, V <sub>GE</sub> =4V	150	Α
Maximum Collector-to-Emitter dv / dt	dV <sub>CE</sub> / dt	V <sub>CE</sub> ≤320V, starting Tch=25°C	400	V / μs
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-40 to +150	°C

<sup>\*:</sup> Concerning dv / dt (slope of Collector Voltage at the time of Turn-OFF), dv / dt > 400 V / µs will be 100% screen-detected in the circuit shown as Fig. 1.

#### **Package Dimensions**

unit : mm (typ) 7011A-004



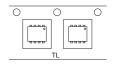
#### **Product & Package Information**

• Package : ECH8

• JEITA, JEDEC :-

• Minimum Packing Quantity : 3000 pcs./reel

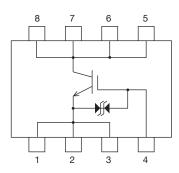
#### Packing Type: TL



#### Marking



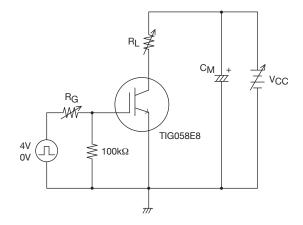
#### **Electrical Connection**



#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit	
Faranieter	Symbol		min	typ	max	Oill	
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I <sub>C</sub> =2mA, V <sub>GE</sub> =0V	400			V	
Collector-to-Emitter Cutoff Current	ICES	V <sub>CE</sub> =320V, V <sub>GE</sub> =0V			10	μΑ	
Gate-to-Emitter Leakage Current	IGES	VGE=±6V, VCE=0V			±10	μΑ	
Gate-to-Emitter Threshold Voltage	V <sub>GE</sub> (off)	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	0.4		0.9	V	
Collector-to-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =100A, V <sub>GE</sub> =4V		4.0	5.6	V	
Input Capacitance	Cies			2200		pF	
Output Capacitance	Coes	V <sub>CE</sub> =10V, f=1MHz		32		pF	
Reverse Transfer Capacitance	Cres			24		pF	

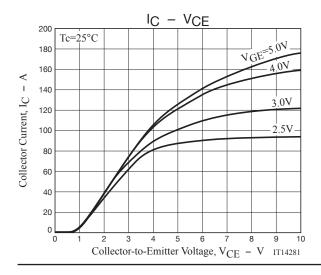
Fig.1 Large Current R Load Switching Circuit

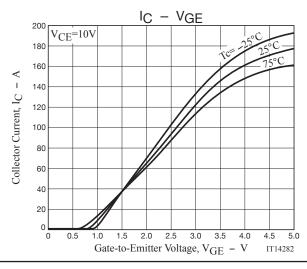


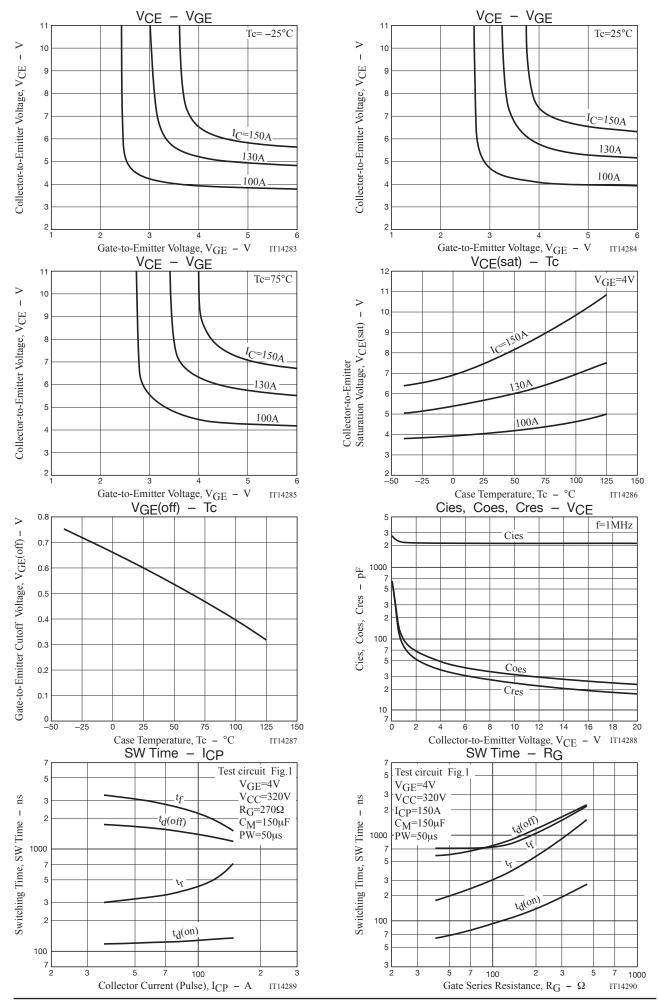
Note1. Gate Series Resistance  $R_G \ge 230\Omega$  is recommended for protection purpose at the time of turn OFF. However, if  $dv / dt \le 400V / \mu s$  is satisfied at customer's actual set evaluation,  $R_G < 230\Omega$  can also be used. Note2. The collector voltage gradient dv / dt must be smaller than  $400V / \mu s$  to protect the device when it is turned off.

## **Ordering Information**

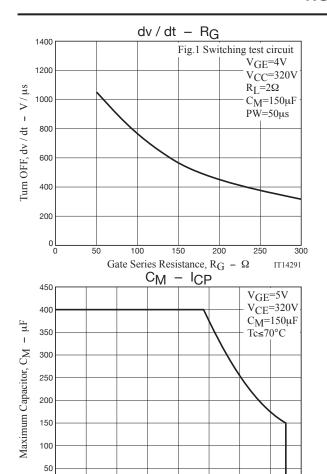
Device	Package	Shipping	memo	
TIG058E8-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free	







## **TIG058E8**



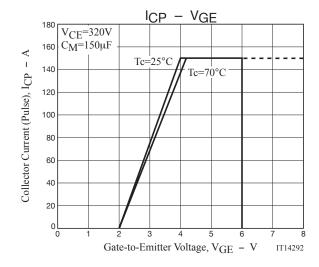
100

Collector Current (Pulse),  $I_{CP} - A$ 

120

IT14293

0

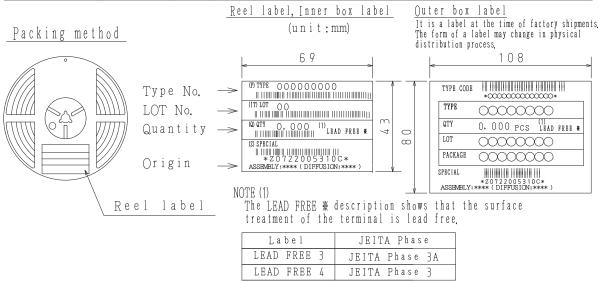


#### **Embossed Taping Specification**

#### TIG058E8-TL-H

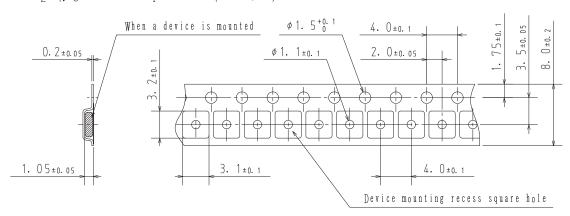
## 1. Packing Format

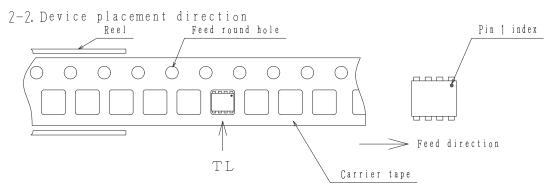
Package Name	Carrier Tape	Maximum Number of devices contained (pcs)			Packing format		
	Туре	Reel	Inner box	Outer box	Inner $BOX(C-1)$	Outer BOX (A-7)	
ECH8	СРН6	3, 000	15, 000	90,000	5 reels contained	6 inner boxes contained	
					Dimensions:mm (external)	Dimensions:mm (external)	
					183×72×185	440×195×210	



# 2. Taping configuration

2-1. Carrier tape size (unit:mm)





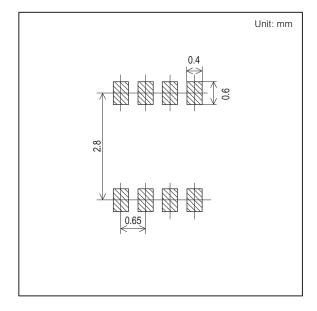
Those with pin 1 index on the feed hole side · · · · · TL

# **Outline Drawing**

TIG05E8-TL-H

# Mass (g) Unit 0.02 \* For reference mm 0. 15<sup>+0. 1</sup><sub>-0. 05</sub> 0. 25±0.06 2. 9±0.06 0~0.02 2. 8±0. 05 2. 3±0.06 LOT No. 0. 25±0.06 0. 3<sup>+0. 1</sup> 0.65 PIN#1 0. 9±0. 05 0.05 \$ \$

# Land Pattern Example



Note: TIG058E8 has protection diode between gate and emitter but handling it requires sufficient care to be taken.

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